

Neil A Moser

List of Publications by Year in descending order

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13
papers

1,400
citations

840119

11
h-index

1199166

12
g-index

13
all docs

13
docs citations

13
times ranked

1122
citing authors

#	ARTICLE	IF	CITATIONS
1	Scaled T-Gate AlGaInGaO_3 MESFETs With 2.45 kV Breakdown and High Switching Figure of Merit. IEEE Electron Device Letters, 2022, 43, 1307-1310.	2.2	8
2	Lateral AlGaInGaO_3 field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	1.0	85
3	Toward high voltage radio frequency devices in AlGaInGaO_3 . Applied Physics Letters, 2020, 117, .	1.5	23
4	Pulsed Power Performance of AlGaInGaO_3 MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	2.2	32
5	RF Power Performance of Sc(Al,Ga)N/GaN HEMTs at Ka-Band. IEEE Electron Device Letters, 2020, 41, 1181-1184.	2.2	41
6	Field-Effect Transistors 1. Springer Series in Materials Science, 2020, , 563-582.	0.4	0
7	Thin channel AlGaInGaO_3 MOSFETs with self-aligned refractory metal gates. Applied Physics Express, 2019, 12, 126501.	1.1	35
8	Recessed-Gate Enhancement-Mode AlGaInGaO_3 MOSFETs. IEEE Electron Device Letters, 2018, 39, 67-70.	2.2	187
9	Donors and deep acceptors in AlGaInGaO_3 . Applied Physics Letters, 2018, 113, .	1.5	203
10	AlGaInGaO_3 MOSFETs for Radio Frequency Operation. IEEE Electron Device Letters, 2017, 38, 790-793.	2.2	248
11	Ge-Doped AlGaInGaO_3 MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778.	2.2	165
12	High pulsed current density AlGaInGaO_3 MOSFETs verified by an analytical model corrected for interface charge. Applied Physics Letters, 2017, 110, .	1.5	75
13	Enhancement-mode AlGaInGaO_3 wrap-gate fin field-effect transistors on native (100) AlGaInGaO_3 substrate with high breakdown voltage. Applied Physics Letters, 2016, 109, .	1.5	298